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SEMICONDUCTOR

2N5638

N-Channel Switch

- This device is designed for low level analog switchng, sample and hold circuits and chopper stabilized amplifiers.
- Sourced from process 51.



1. Drain 2. Source 3. Gate

Absolute Maximum Ratings * T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{DG}	Drain-Gate Voltage	30	V
V _{GS}	Gate-Source Voltage	-30	V
I _{GF}	Forward Gate Current	50	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ +150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Chara	Off Characteristics					
V _{(BR)GSS}	Gate-Source Breakdown Voltage	$V_{DS} = 0, I_{G} = -10\mu A$	-30			V
I _{GSS}	Gate Reverse Current	$V_{GS} = -15V, V_{DS} = 0$			-1.0	nA
I _{D(off)}	Drain Cutoff Leakage Current	V _{DS} = 12V, V _{GS} = 15V			1.0	nA
On Characteristics						
I _{DSS}	Zero-Gate Voltage Drain Current *	$V_{DS} = 20V, I_{GS} = 0$	50			mA
r _{DS(on)}	Drain-Source On Resistance	$V_{GS} = 0V, I_{D} = 1.0mA$			30	Ω
Small Signal Characteristics						
r _{ds(on)}	Drain-Source On Resistance	$V_{DS} = V_{GS} = 0, f = 1.0 \text{kHz}$			30	Ω
C _{iss}	Input Capacitance	V _{DS} = 0, V _{GS} = 12V, f = 1.0MHz			10	pF
C _{rss}	Reverse Transfer Capacitance	V _{DS} = 0V, V _{GS} = 12V, f = 1.0MHz			4.0	pF
Switching Characteristics						
t _{d(on)}	Trun On Delay Time	$V_{DD} = 10V, V_{GS(on)} = 0$			4.0	ns
t _r	Rise Time	$V_{GS(off)} = -12, I_{D(on)} = 12mA$ $R_G = 50\Omega$			5.0	ns
t _{d(off)}	Trun Off Delay Time			5.0	ns	
t _f	Fall Time	1			10	ns

* Pulse Test: Pulse Width $\leq 300 \mu s, \, Duty \, Cycle \leq 1.0\%$

Thermal Characteristics T_A=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

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CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
DOME™	GlobalOptoisolator™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E ² CMOS [™]	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	I ² C [™]	OCX™	RapidConfigure™	UHC™
Across the board.	Around the world. [™]	OCXPro™	RapidConnect™	UltraFET [®]
The Power Franchise™		OPTOLOGIC®	SILENT SWITCHER [®]	VCX™
Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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